introducing a metal element capable of promoting crystallization of the amorphous semiconductor film to form a metal element added region;

crystallizing the amorphous semiconductor film to cause crystal growth to proceed in a crystal growth direction parallel to the insulating surface from the metal element added region thereby forming a crystalline semiconductor film;

patterning the crystalline semiconductor film to form at least a crystalline semiconductor island in which carriers move in a carrier moving direction identical with the crystal growth direction,

wherein the metal element added region is separated from the crystalline semiconductor island by a distance, and

wherein the metal element added region has a length that extends beyond an end portion of the crystalline semiconductor island in a longitudinal direction of the metal element added region.

7. (Amended) A method according to claim 6,

wherein the length of the metal element added region is set to 50% or more of a crystal growth distance.

8. (Amended) A method according to claim 6, wherein the metal element comprises at least one element selected from Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

9. (Amended) A method of manufacturing a semiconductor device, said method comprising:

forming an amorphous semiconductor film on an insulating surface;

selectively introducing a metal element capable of promoting crystallization of the amorphous semiconductor film into at least a first region and a second region of the amorphous semiconductor film to form a first metal element introduced region and a second metal element introduced region, respectively;

crystallizing the amorphous semiconductor film to cause crystal growth to proceed in parallel to the insulating surface from each of the first and second metal element introduced regions to form a first crystalline semiconductor region and a second crystalline semiconductor region;

forming at least an active region of the semiconductor device in the first crystalline semiconductor region without

forming an active region at the second crystalline semiconductor region.

10. (Amended) A method according to claim 9, wherein the metal element comprises at least one element selected from Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

11. (Amended) A method according to claim 9, wherein the metal element is introduced by an ion implanting method.

12. (Amended) A method according to claim 9, wherein the metal element is introduced by coating a solvent comprising the metal element.

Please add claims 14-23.

14. (New) A method according to claim 9, wherein the semiconductor film comprises silicon.

15. (New) A method according to claim 9,

wherein the semiconductor device includes at least one element selected from the group consisting of an n-channel thin film transistor and a p-channel thin film transistor,

wherein the n-channel thin film transistor has a first S value not higher than 90 mV/dec and the p-channel thin film transistor has a second S value not higher than 100 mV/dec.

16. (New) A method according to claim 9,

wherein the semiconductor device includes at least one element selected from the group consisting of an n-channel thin film transistor and a p-channel thin film transistor,

wherein the n-channel thin film transistor has a first S value not lower than 75 mV/dec and the p-channel thin film transistor has a second S value not lower than 75 mV/dec.

17. (New) A method according to claim 9,

wherein the semiconductor device is used in one or more of a portable telephone, a video camera, a mobile computer, a head mount display, a rear type projector, and a front type projector.

18. (New) A method according to claim 6, wherein the semiconductor film comprises silicon.

19. (New) A method according to claim 6,

wherein the metal element comprises at least one element selected from Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

20. (New) A method according to claim 6,

wherein the semiconductor device comprises one or both of an n-channel thin film transistor and a p-channel thin film transistor,

wherein the n-channel thin film transistor has a first S value not higher than 90 mV/dec and the p-channel thin film transistor has a second S value not higher than 100 mV/dec.

21. (New) A method according to claim 6,

wherein the semiconductor device comprises one or both of an n-channel thin film transistor and a p-channel thin film transistor,

wherein the n-channel thin film transistor has a first S value not lower than 75 mV/dec and the p-channel thin film transistor has a second S value not lower than 75 mV/dec.

22. (New) A method according to claim 6,

wherein the semiconductor device is used in one or more of a portable telephone, a video camera, a mobile computer, a head mount display, a rear type projector, and a front type projector.

A2 cont. claim 9

23. (New) A method according to claim 9 further comprising controlling crystal growth state using the second metal element introduced region.